



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>

PN3638A

Silicon PNP Transistor Audio Amplifier, Switch TO-92 Type Package

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$, Note 1 unless otherwise specified)

Collector-Emitter Voltage, V_{CEO}	25V
Collector-Base Voltage, V_{CBO}	25V
Emitter-Base Voltage, V_{EBO}	4.9V
Continuous Collector Current, I_C	800mA
Total Device Dissipation ($T_A = 25^\circ\text{C}$), P_D	625mW
Derate Above 25°C	5mW/ $^\circ\text{C}$
Operating Junction Temperature Range, T_J	-55° to $+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-55° to $+150^\circ\text{C}$
Thermal Resistance, Junction to Case, $R_{\theta JC}$	83.3 $^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient, $R_{\theta JA}$	200 $^\circ\text{C}/\text{W}$

Note 1. These ratings are limiting values above which the serviceability of any semiconductor device may be impaired and are based on a maximum junction temperature of $+150^\circ\text{C}$.

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}$, $I_B = 0$, Note 2	25	-	-	V
	$V_{(BR)CES}$	$I_C = 100\mu\text{A}$, $I_B = 0$, Note 2	25	-	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}$, $I_E = 0$	25	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}$, $I_C = 0$	4	-	-	V
Collector Cutoff Current	I_{CES}	$V_{CE} = 15\text{V}$, $I_E = 0$	-	-	35	nA
		$V_{CE} = 15\text{V}$, $I_E = 0$, $T_A = +65^\circ\text{C}$	-	-	2	μA
ON Characteristics (Note 2)						
DC Current Gain	h_{FE}	$V_{CE} = 1\text{V}$, $I_C = 50\text{mA}$	100	-	-	
		$V_{CE} = 2\text{V}$, $I_C = 300\text{mA}$	20	-	-	
		$V_{CE} = 10\text{V}$, $I_C = 100\text{mA}$	80	-	-	
		$V_{CE} = 10\text{V}$, $I_C = 1\text{mA}$	100	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}$, $I_B = 2.5\text{mA}$	-	-	0.25	V
		$I_C = 300\text{mA}$, $I_B = 30\text{mA}$	-	-	1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 50\text{mA}$, $I_B = 2.5\text{mA}$	-	-	1.1	V
		$I_C = 300\text{mA}$, $I_B = 30\text{mA}$	0.8	-	2.0	V

Note 2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

Electrical Characteristics (Cont'd): ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Small Signal Characteristics						
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, f = 1\text{MHz}$	-	-	10	pF
Input Capacitance	C_{ib}	$V_{BE} = 0.5\text{V}, f = 1\text{MHz}$	-	-	25	pF
Small-Signal Current Gain	h_{fe}	$I_C = 50\text{mA}, V_{CE} = 3\text{V}, f = 100\text{MHz}$	1.5	-	-	
		$I_C = 10\text{mA}, V_{CE} = 10\text{V}, f = 1\text{kHz}$	100	-	-	
Input Impedance	h_{ie}	$I_C = 10\text{mA}, V_{CE} = 10\text{V}, f = 1\text{kHz}$	-	-	2	$\text{k}\Omega$
Output Admittance	h_{oe}		-	-	1.2	μmhos
Voltage Feedback Ratio	h_{re}		-	-	15	$\times 10^{-4}$
Switching Characteristics						
Turn-On Time	t_{on}	$V_{CC} = 10\text{V}, I_C = 300\text{mA}, I_{B1} = 30\text{mA}$	75	-	-	ns
Delay Time	t_d		20	-	-	ns
Rise Time	t_r		70	-	-	ns
Turn-Off Time	t_{off}	$V_{CC} = 10\text{V}, I_C = 300\text{mA}, I_{B1} = I_{B2} = 30\text{mA}$	170	-	-	ns
Storage Time	t_s		140	-	-	ns
Fall Time	t_f		70	-	-	ns

